MAX.

45CTF

45

0.57

15

UNIT

V

V

А

Rectifier diodes schottky barrier

PBYR1545CTF series

MAX.

40CTF

40

0.57

15

GENERAL DESCRIPTION

Dual low leakage, platinum barrier, schottky rectifier diodes in a full pack plastic envelope, featuring low forward voltage drop, absence of stored charge. and guaranteed reverse surge capability. The devices are intended for use in switched mode power supplies and high frequency circuits in general where low conduction and zero switching losses are important.

DESCRIPTION

PINNING - SOT186

anode 1 (a)

cathode (k)

anode 2 (a)

PIN

1

2

3

case

PIN CONFIGURATION

QUICK REFERENCE DATA

voltage

PARAMETER

Forward voltage

Repetitive peak reverse

Average output current

(both diodes conducting)

SYMBOL

 V_{RRM}

 V_{F}

I_{O(AV)}

SYMBOL

MAX.

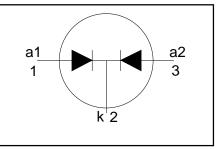
35CTF

35

0.57

15

PBYR15-



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V _{RRM} V _{RWM} V _R	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage	T _{hs} ≤ 117 °C		-35 35 35 35	-40 40 40 40	-45 45 45 45	V V V
I _{O(AV)}	Average output current (both diodes conducting)	square wave; δ = 0.5; T _{bs} ≤ 100 °C	-		15		A
I _{O(RMS)}	RMS output current (both diodes conducting)		-		20		A
I _{FRM}	Repetitive peak forward current	t = 25 μs; δ = 0.5; T _{hs} ≤ 100 °C	-		15		A
I _{FSM}	Non-repetitive peak forward current, per diode	t = 10 ms t = 8.3 ms sinusoidal $T_i = 125$ °C prior to surge; with reapplied $V_{RRM(max)}$	-		100 110		A A
l ² t	I ² t for fusing	t = 10 ms	-		50		A ² s
I _{RRM}	Repetitive peak reverse current per diode.		-		1		A
I _{RSM}	Non-repetitive peak reverse current per diode.	t _p = 100 μs	-		1		A
T _{stg} T _j	Storage temperature Operating junction temperature		-65 -		175 150		°C C

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PBYR1545CTF series

ISOLATION LIMITING VALUE & CHARACTERISTIC

 $T_{hs} = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	Repetitive peak voltage from all three terminals to external heatsink	$R.H. \leq 65\%$; clean and dustfree	-		1500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	12	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	per diode both diodes	-	-	6.1 5.2	K/W K/W
R _{th j-a}	Thermal resistance junction to ambient	(with heatsink compound) in free air.	-	55	-	K/W

STATIC CHARACTERISTICS

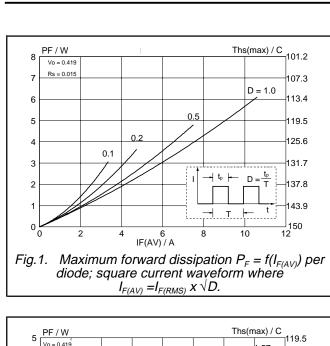
 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage (per diode)	I _F = 7.5 A; T _j = 125°C I _F = 15 A; T _i = 125°C	-	0.50 0.62	0.57 0.72	
		I _F = 15 A	-	0.74	0.84	V
I _R	Reverse current (per diode)	$V_{R} = V_{RRM}$ $V_{R} = V_{RRM}$ T = 125 °C	-	50 12	100 22	μA mA
C _d	Junction capacitance (per diode)	$V_{R}^{A} = V_{RRM}^{AAAA}; T_{j} = 125 ^{\circ}C$ f = 1MHz; $V_{R} = 5V; T_{j} = 25 ^{\circ}C$ to 125 $^{\circ}C$	-	350	-	pF

Rectifier diodes

schottky barrier

PBYR1545CTF series



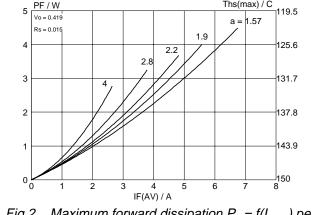
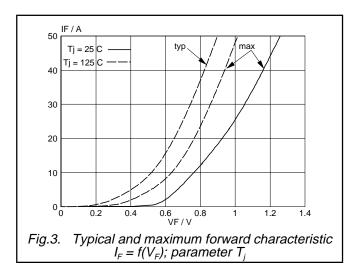
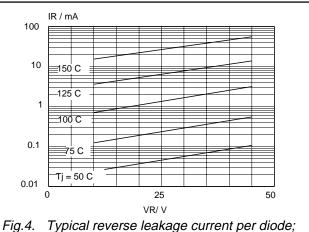
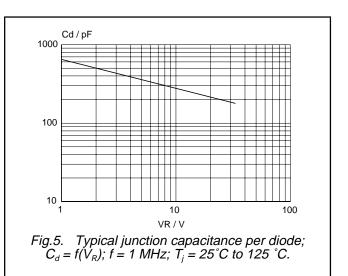


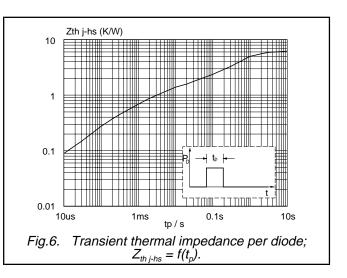
Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form factor = $I_{F(RMS)} / I_{F(AV)}$.





 I_{g} . I ypical reverse leakage current per diode $I_{R} = f(V_{R})$; parameter T_{j}



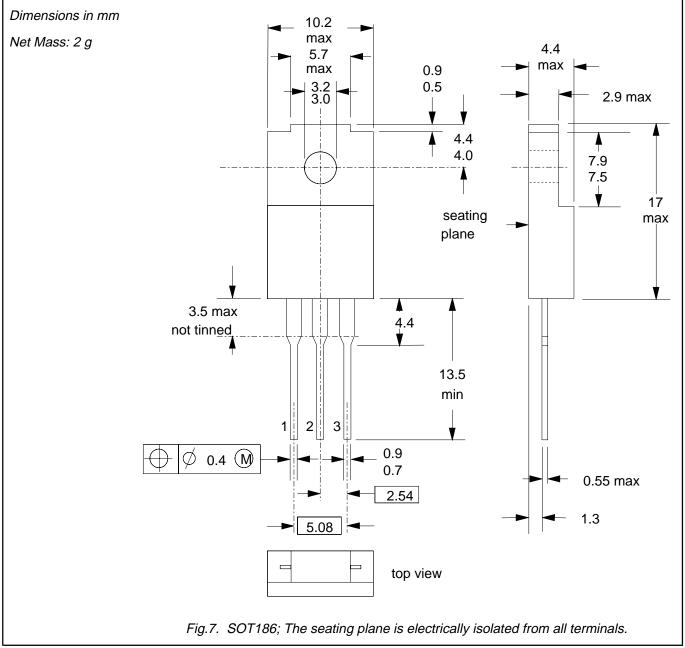


Rectifier diodes schottky barrier

Product specification

PBYR1545CTF series

MECHANICAL DATA



Notes

Refer to mounting instructions for F-pack envelopes.
Epoxy meets UL94 V0 at 1/8".

Rectifier diodes schottky barrier

PBYR1545CTF series

DEFINITIONS

Data sheet status				
Objective specification This data sheet contains target or goal specifications for product development.				
Preliminary specification This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.			
Limiting values				
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.				
Application information				

Where application information is given, it is advisory and does not form part of the specification.

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